Supporting Information

Impact of molecular planarity on electronic devices in thienoisindigo-based organic semiconductors

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Fig. S1  (a) TGA curves of 1-3 at the heating rate of 10 °C / min under a nitrogen atmosphere. (b) DSC curves of 1-3 at the scan rate of 5 °C / min under a nitrogen atmosphere.
Fig. S2  (a) p-channel and (b) n-channel output characteristics of a top contact device of 1 prepared on a TTC modified substrate.
Fig. S3  XRD patterns of 1 thermally evaporated films on (a) bare, (b) HMDS, and (c) OTMS substrates.  XRD patterns of 2 on (d) bare, (e) HMDS, and (f) OTMS substrates.  XRD patterns of 3 on (g) bare, (h) HMDS, and (i) OTMS substrates.
**Fig. S4**  AFM images of 1 thermally evaporated on (a) bare, (b) HMDS, and (c) OTMS substrates.

AFM images of 2 on (d) bare, (e), HDMS, and (f) OTMS substrates.  AFM images of 3 on (g) bare, (h) HMDS, and (i) OTMS substrates.
Fig. S5  XRD patterns of blended films of 1 (a) as cast, and after annealing at (b) 80 °C, (c) 110 °C, and (d) 150 °C.  XRD patterns of blended films of 2 (e) as cast, and after annealing at (f) 80 °C, (g) 110 °C, and (h) 150 °C.  XRD patterns of blended films of 3 (i) as cast, and after annealing at (j) 80 °C, (k) 110 °C, and (l) 150 °C.